April 2017



# FFP30S60S 30 A, 600 V STEALTH<sup>TM</sup> II Diode

#### Features

- Stealth Recovery trr = 40 ns (@ IF = 30 A)
- Max Forward Voltage, VF = 2.6 V (@ TC = 25°C)
- 600 V Reverse Voltage and High Reliability
- Avalanche Energy Rated
- RoHS Compliant

# Applications

- General Purpose
- SMPS, Power Switching Circuits
- Boost Diode in Continuous Mode Power Factor Corrections

#### **Pin Assigments**



# Description

The FFP30S60S is a STEALTH<sup>™</sup> II diode with soft recovery characteristics. It is silicon nitride passivated ion-implanted epitaxial planar construction.

This device is intended for use as freewheeling of boost diode in switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.



1. Cathode 2. Anode

## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Rating	Unit	
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	600	V	
V <sub>RWM</sub>	Working Peak Reverse Voltage	600	V	
V <sub>R</sub>	DC Blocking Voltage	600	V	
I <sub>F(AV)</sub>	Average Rectified Forward Current $@T_{C} = 103^{\circ}C$	30	Α	
I <sub>FSM</sub>	Non-repetitive Peak Surge Current 60Hz Single Half-Sine Wave	300	А	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-65 to +175	°C	

### **Thermal Characteristics**

Symbol	Parameter	Max.	Unit
$R_{ ext{ heta}JC}$	Maximum Thermal Resistance, Junction to Case	1.1	°C/W

# Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFP30S60STU	F30S60S	TO-220-2L	Tube	N/A	N/A	50

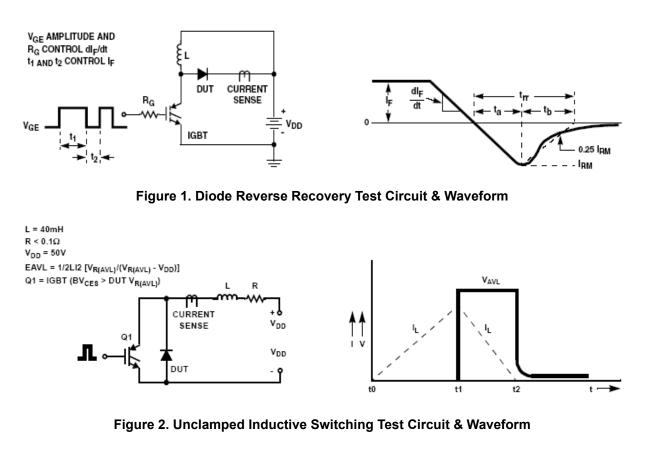
1

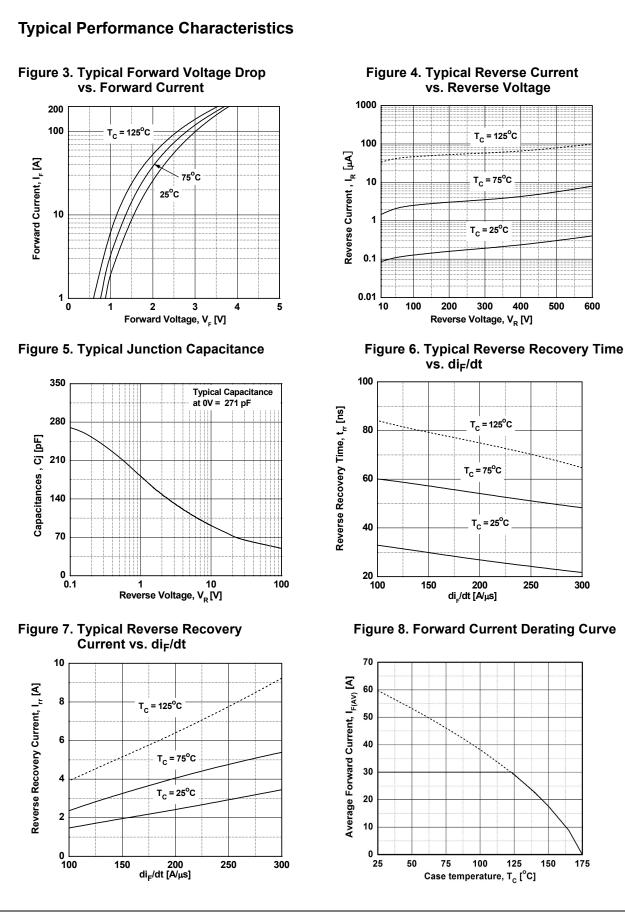
FFP30S60S — STEALTH<sup>TM</sup> II Diode

Symbol	Parameter	Min.	Тур.	Max.	Unit	
V <sub>FM</sub> 1	I <sub>F</sub> = 30 A I <sub>F</sub> = 30 A	T <sub>C</sub> = 25°C T <sub>C</sub> = 125°C		2.1 1.6	2.6	V
I <sub>RM</sub> 1	V <sub>R</sub> = 600 V V <sub>R</sub> = 600 V	T <sub>C</sub> = 25°C T <sub>C</sub> = 125°C	-	-	100 500	μA
t <sub>rr</sub>	I <sub>F</sub> = 1 A, di <sub>F</sub> /dt = 100 A/μs, V <sub>R</sub> = 30 V	T <sub>C</sub> = 25°C	-	25	35	ns
t <sub>rr</sub> I <sub>rr</sub> S factor Q <sub>rr</sub>	I <sub>F</sub> = 30 A, di <sub>F</sub> /dt = 200 A/µs, V <sub>R</sub> = 390 V	T <sub>C</sub> = 25°C	- - -	28 2.4 0.9 34	40 - - -	ns A nC
t <sub>rr</sub> I <sub>rr</sub> S factor Q <sub>rr</sub>	I <sub>F</sub> = 30 A, di <sub>F</sub> /dt = 200 A/µs, V <sub>R</sub> = 390 V	T <sub>C</sub> = 125 <sup>o</sup> C	- - -	75 6.3 0.9 236		ns A nC
W <sub>AVL</sub>	Avalanche Energy ( $L = 40 \text{ mH}$ )	20	-	-	mJ	

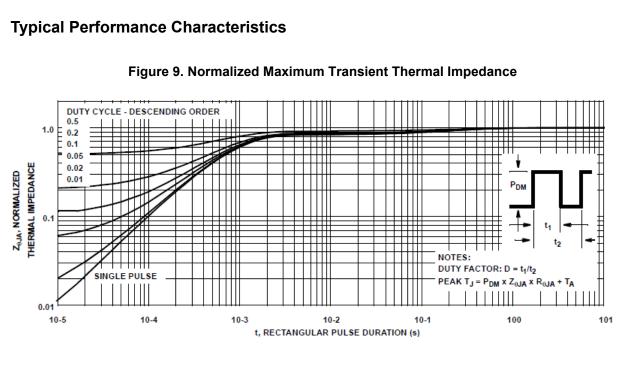
1: Pulse: Test Pulse width = 300µs, Duty Cycle = 2%

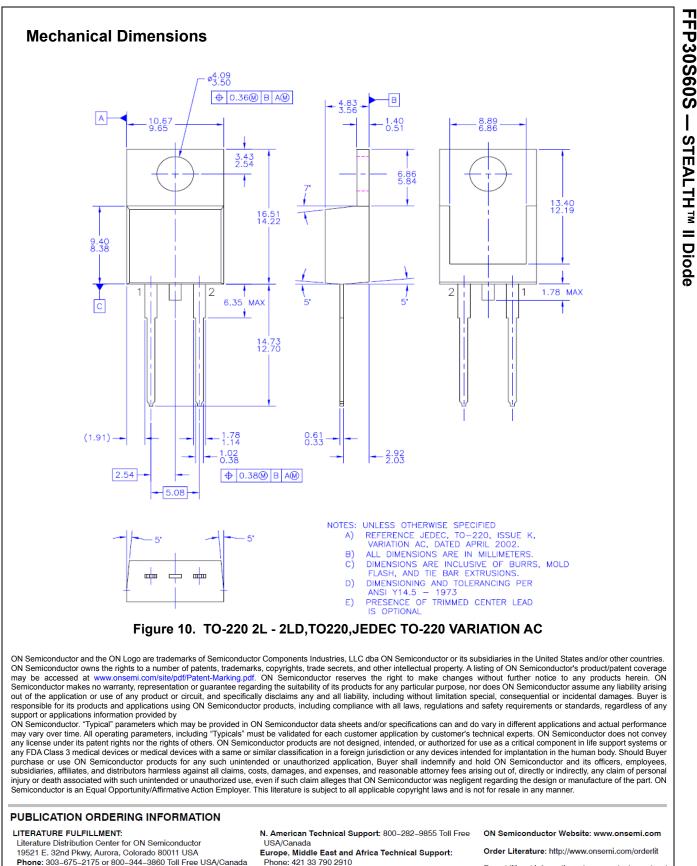
### **Test Circuit and Waveforms**





FFP30S60S — STEALTH™ II Diode





For additional information, please contact your local Sales Representative

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